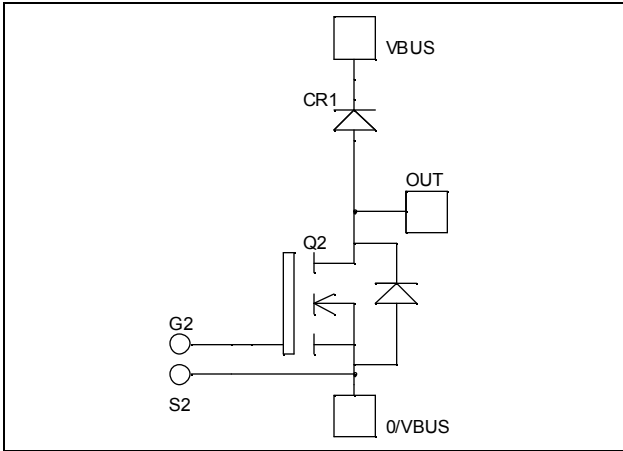


***Boost chopper  
MOSFET Power Module***

**$V_{DSS} = 100V$   
 $R_{DSon} = 2.25m\Omega$  typ @  $T_j = 25^\circ C$   
 $I_D = 495A$  @  $T_c = 25^\circ C$**



**Application**

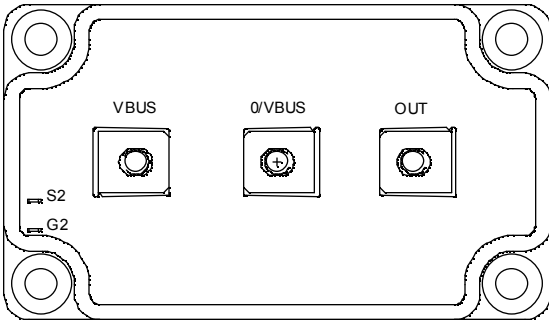
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

**Features**

- Power MOS V<sup>®</sup> MOSFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

**Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile



**Absolute maximum ratings**

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	100	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	495
		$T_c = 80^\circ C$	370
$I_{DM}$	Pulsed Drain current	1900	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	2.5	m $\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	1250
$I_{AR}$	Avalanche current (repetitive and non repetitive)	100	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3000	

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

## Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 100V$			400	$\mu\text{A}$
		$V_{GS} = 0V, V_{DS} = 80V$			2000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 200A$		2.25	2.5	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 10\text{mA}$	2		4	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 400$	nA

## Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		40		nF
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		15.7		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		5.9		
$Q_g$	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 50V$ $I_D = 400A$		1360		nC
$Q_{gs}$	Gate – Source Charge			240		
$Q_{gd}$	Gate – Drain Charge			720		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching</b> $V_{GS} = 15V$ $V_{Bus} = 66V$ $I_D = 400A$ $R_G = 1.25\Omega$		160		ns
$T_r$	Rise Time			240		
$T_{d(off)}$	Turn-off Delay Time			500		
$T_f$	Fall Time			160		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ 25°C</b> $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 400A, R_G = 1.25\Omega$		2.2		mJ
$E_{off}$	Turn-off Switching Energy ❷			2.41		
$E_{on}$	Turn-on Switching Energy ❶	<b>Inductive switching @ 125°C</b> $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 400A, R_G = 1.25\Omega$		2.43		mJ
$E_{off}$	Turn-off Switching Energy ❷			2.56		

❶  $E_{on}$  includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

## Chopper diode ratings and characteristics

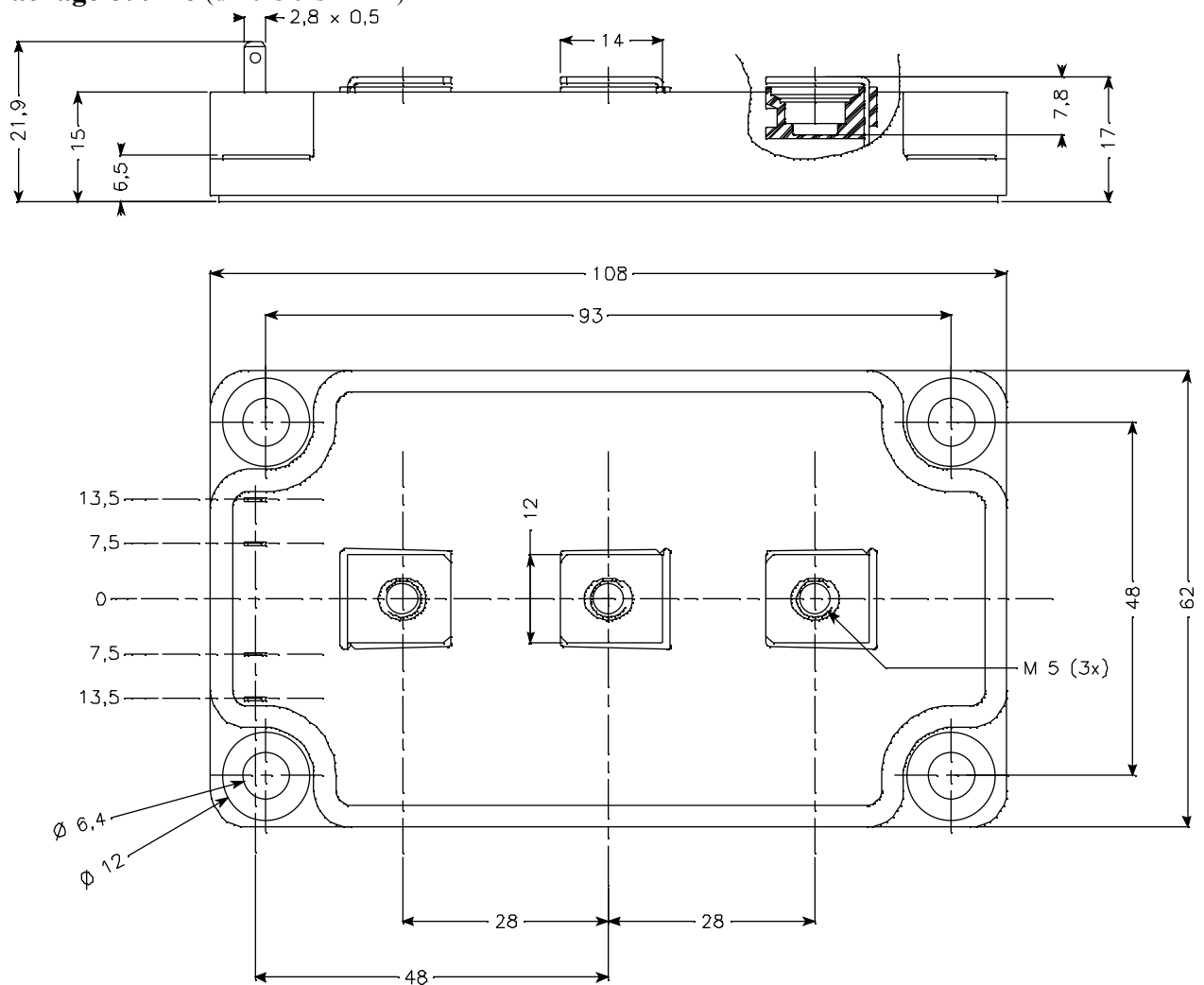
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 200V$	$T_j = 25^\circ\text{C}$		750	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		1000	
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle		400		A
$V_F$	Diode Forward Voltage	$I_F = 400A$		1		V
		$I_F = 800A$		1.4		
		$I_F = 400A$	$T_j = 125^\circ\text{C}$	0.9		
$t_{rr}$	Reverse Recovery Time	$I_F = 400A$ $V_R = 133V$ $di/dt = 800A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	60		ns
	$T_j = 125^\circ\text{C}$		110			
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$	800		nC
			$T_j = 125^\circ\text{C}$	3360		

**Thermal and package characteristics**

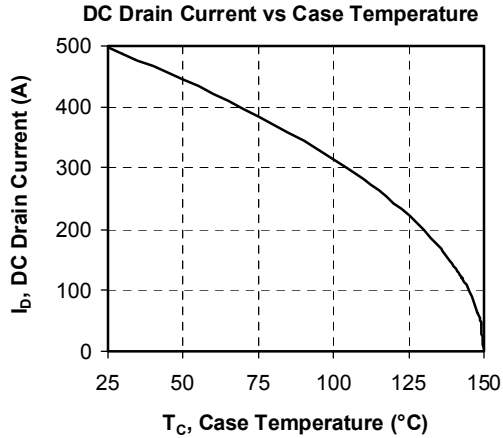
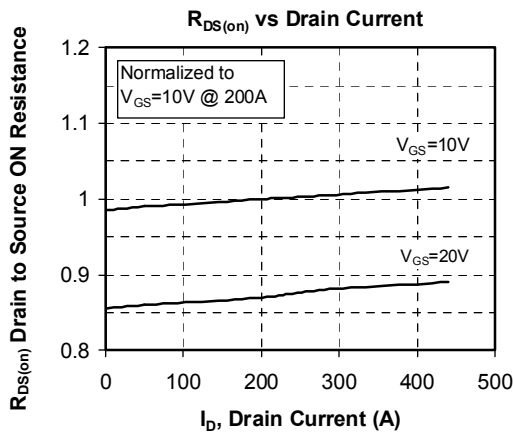
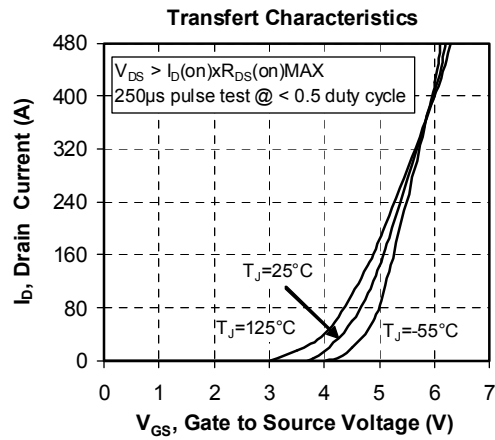
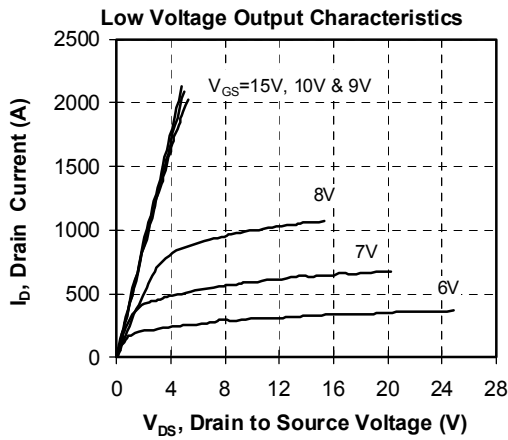
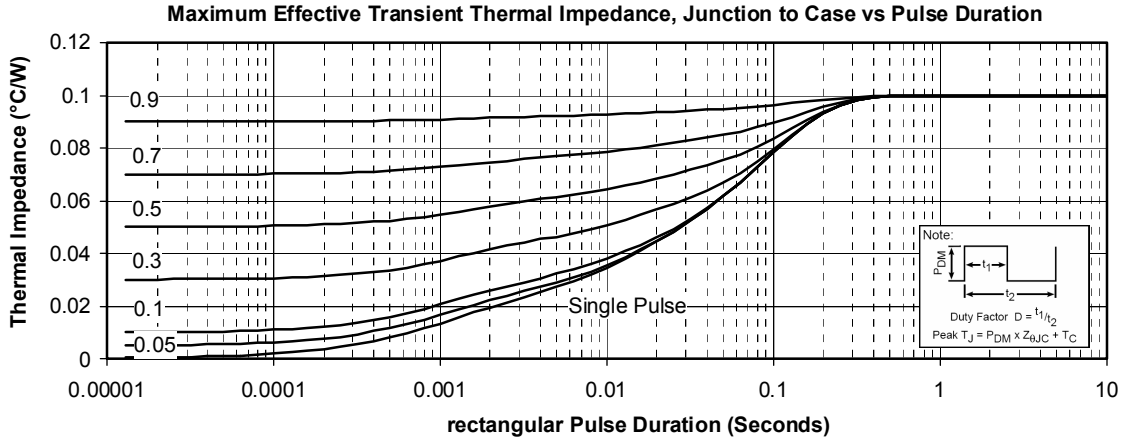
*Symbol Characteristic*

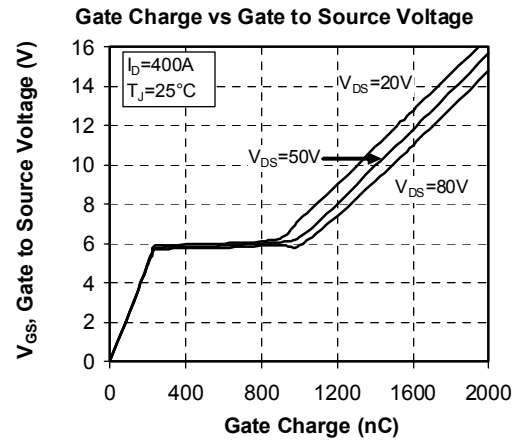
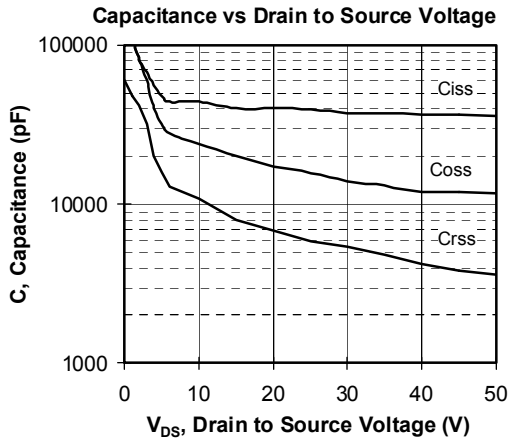
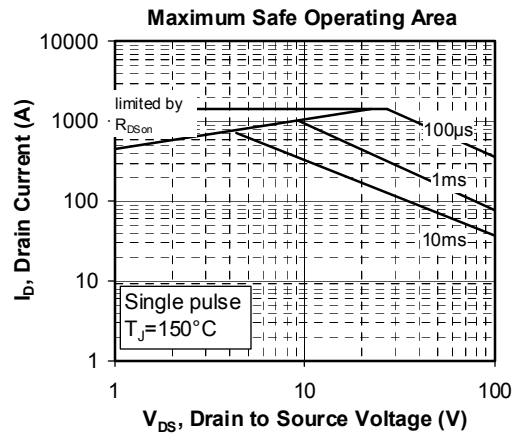
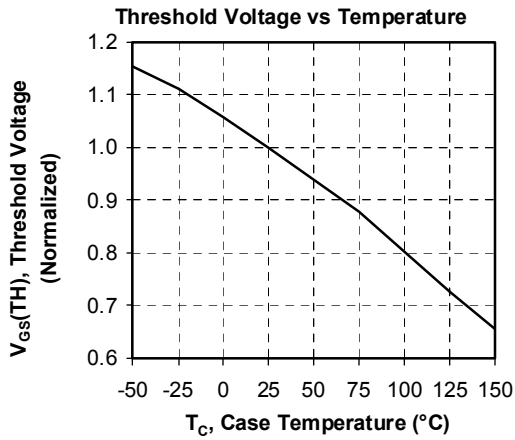
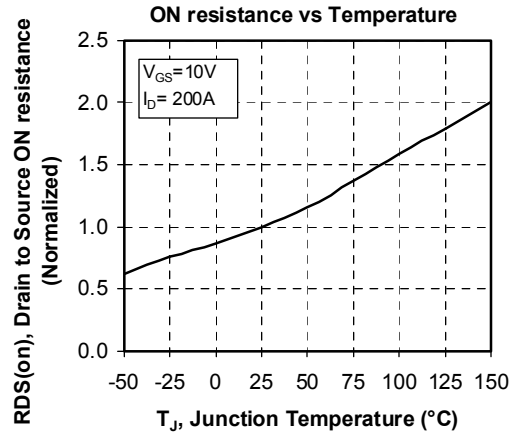
			<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R <sub>thJC</sub>	Junction to Case	Transistor			0.1	°C/W
		Diode			0.14	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, I <sub>Isol</sub> <1mA, 50/60Hz		2500			V
T <sub>J</sub>	Operating junction temperature range		-40		150	°C
T <sub>STG</sub>	Storage Temperature Range		-40		125	
T <sub>C</sub>	Operating Case Temperature		-40		100	
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package Weight				280	g

**Package outline (dimensions in mm)**

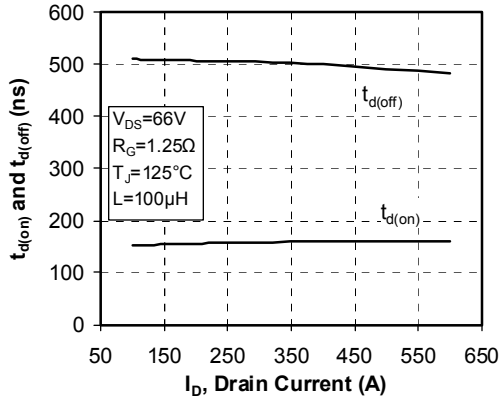


**Typical Performance Curve**

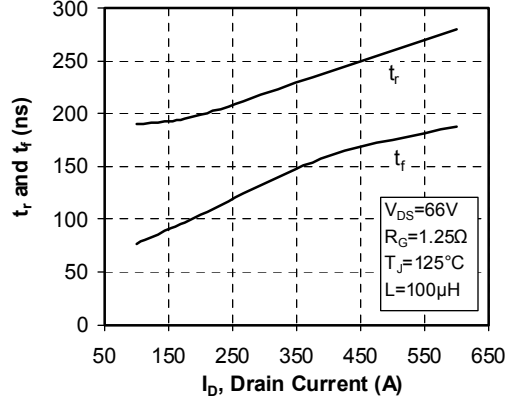




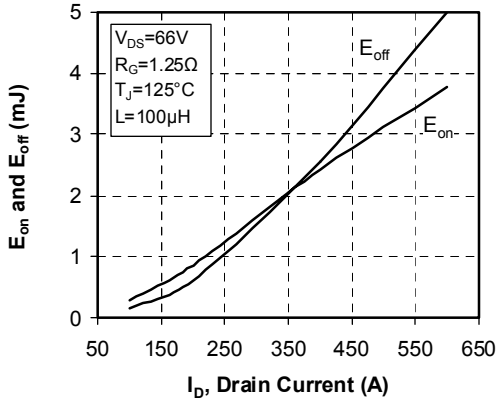
**Delay Times vs Current**



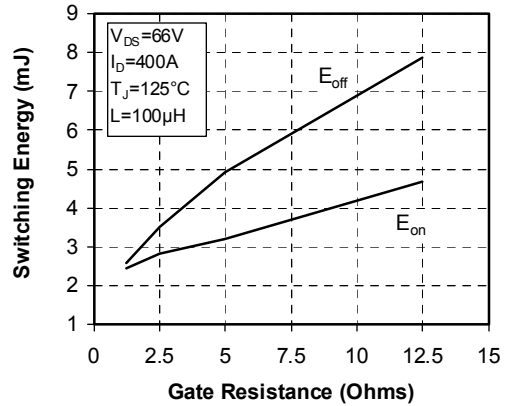
**Rise and Fall times vs Current**



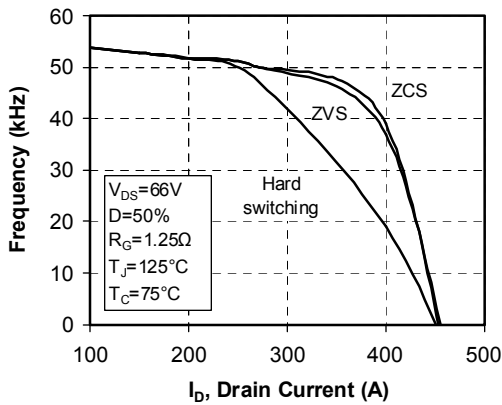
**Switching Energy vs Current**



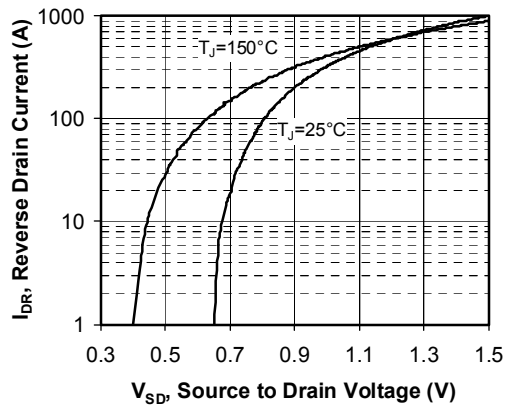
**Switching Energy vs Gate Resistance**



**Operating Frequency vs Drain Current**



**Source to Drain Diode Forward Voltage**



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.